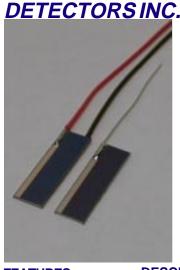
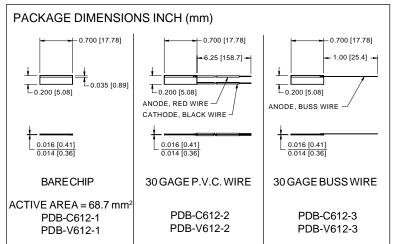
PHOTONIC Silicon Photodiode, Blue Enhanced Solderable Chips

Photoconductive Type PDB-C612 Photovoltaic Type PDB-V612





FEATURES

- Blue enhanced
- Photovoltaic type
- Photoconductive type
- High quantum efficiency

DESCRIPTION: Low cost blue enhanced planar diffused

silicon solderable photodiode. The PDB-V612 cell is designed for low noise, photovoltaic applications. The PDB-C612 cell is

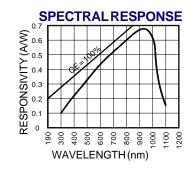
designed for low capacitance, high speed, photoconductive operation. They are available bare, PVC or buss wire leads.

APPLICATIONS

- Optical encoder
- Position sensor
- Industrial controls
- Instrumentation

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER .	PDB-	C612	PDB-	V612	UNITS
01111202		MIN	MAX	MIN	MAX	00
VBR	Reverse Voltage		75		25	V
T _{STG}	Storage Temperature	-40	+125	-40	+125	∘C
To	Operating Temperature Range	-40	+100	-40	+100	°C
Ts	Soldering Temperature		+224		+224	°C
I _L	Light Current		500		500	mA



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	PDB-C612			PDB-V612			LINITO
			MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	810	900		720	800		μ A
ΙD	Dark Current	H = 0, V _R = 5 V*		75	150		40	80	nA
Rsн	Shunt Resistance	H = 0, V _R = 10 mV	5	10		7	15		$M\Omega$
TC Rsh	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8			-8		%/°C
C₁	Junction Capacitance	H = 0, V _R = 5 V**		300			9000		рF
λrange	Spectral Application Range	Spot Scan	350		1100	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		940			940		nm
VBR	Breakdown Voltage	I = 10 μA	25	50		5	15		V
NEP	Noise Equivalent Power	V _R = 0 V @ Peak	7.0 x 10 ⁻¹³ TYP		2.16 x 10 ⁻¹³ TYP			W/ √Hz	
tr	Response Time	RL = 1 K Ω V _R = 5 V**		45			2800		nS